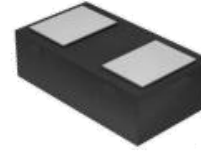




1. Features

- Capacitance: 80pF(Max.)
- Reverse Working Voltage: 4.5V
- IEC 61000-4-2 (ESD Air): ±30KV
IEC 61000-4-2 (ESD Contact): ±30KV
IEC 61000-4-5 (Lightning 8/20μs): 35A

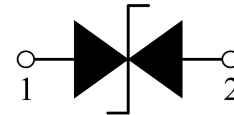
2. Pin Description



3. Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

4. Schematic Diagram



5. Order Information

Type	Package	Size (mm)	Delivery Form	Delivery Quantity
PESD4V5F1BL	DFN1006	1.00x0.60x0.37	7" T&R	10,000

6. Limiting Values(T_A = 25 °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Max	Unit
V _{ESD}	Electrostatic Discharge Voltage	IEC 61000-4-2; Contact Discharge	-	±30	kV
		IEC 61000-4-2; Air Discharge	-	±30	kV
P _{PP}	Peak Pulse Power	t _p = 8/20 μs	-	315	W
I _{PPM}	Rated Peak Pulse Current	t _p = 8/20 μs	-	35	A
T _A	Ambient Temperature Range	-	-55	150	°C
T _{stg}	Storage Temperature Range	-	-55	150	°C

7. Electrical Characteristics(T_A = 25 °C, unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ.	Max	Unit
V _{RWM}	Reverse Working Voltage	T _A = 25 °C	-	-	4.5	V
V _{BR}	Breakdown Voltage	I _R = 1mA; T _A = 25 °C	5.0	-	6.5	V
I _R	Reverse Leakage Current	V _{RWM} = 4.5V; T _A = 25 °C	-	-	1	uA
V _C	Clamping Voltage	I _{PP} =10A, t _p =8/20μs	-	-	6	V
		I _{PP} =35A, t _p =8/20μs	-	-	9	V
C _J	Junction Capacitance	V _R = 0V, f = 1 MHz	-	-	80	pF



8. Typical Characteristics

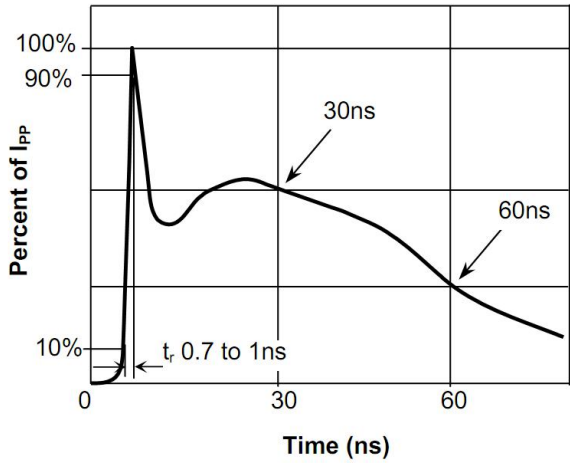


Fig.1 Pulse Waveform-ESD (IEC61000-4-2)

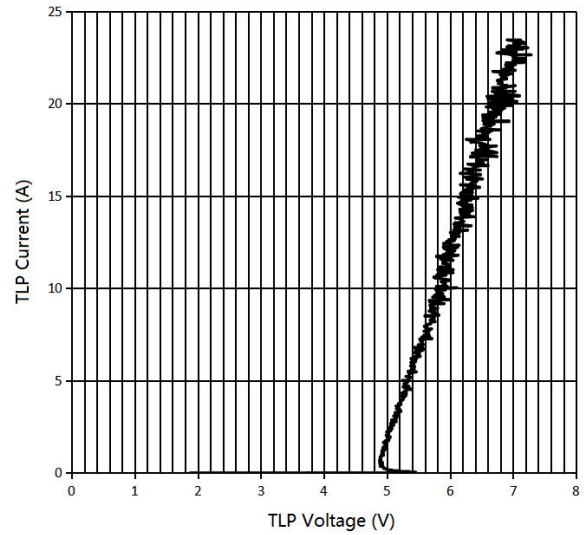


Fig.2 Transmission Line Pulse (TLP)

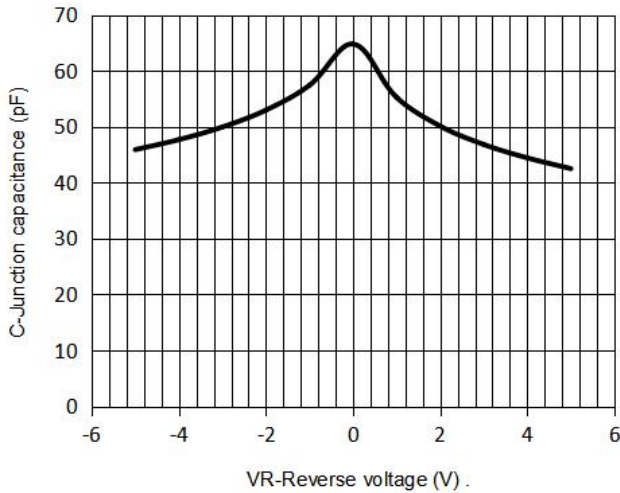


Fig.3 Capacitance vs. Reverse Voltage

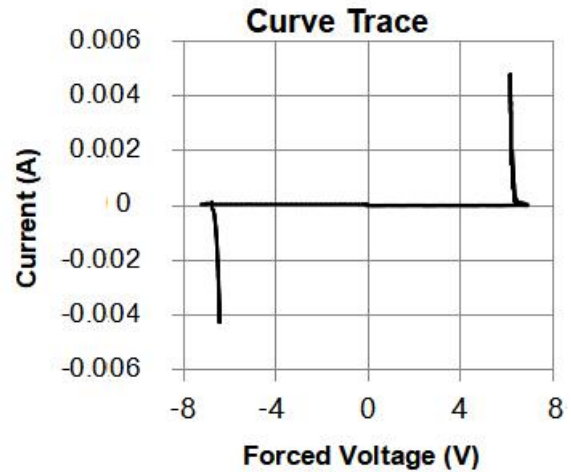
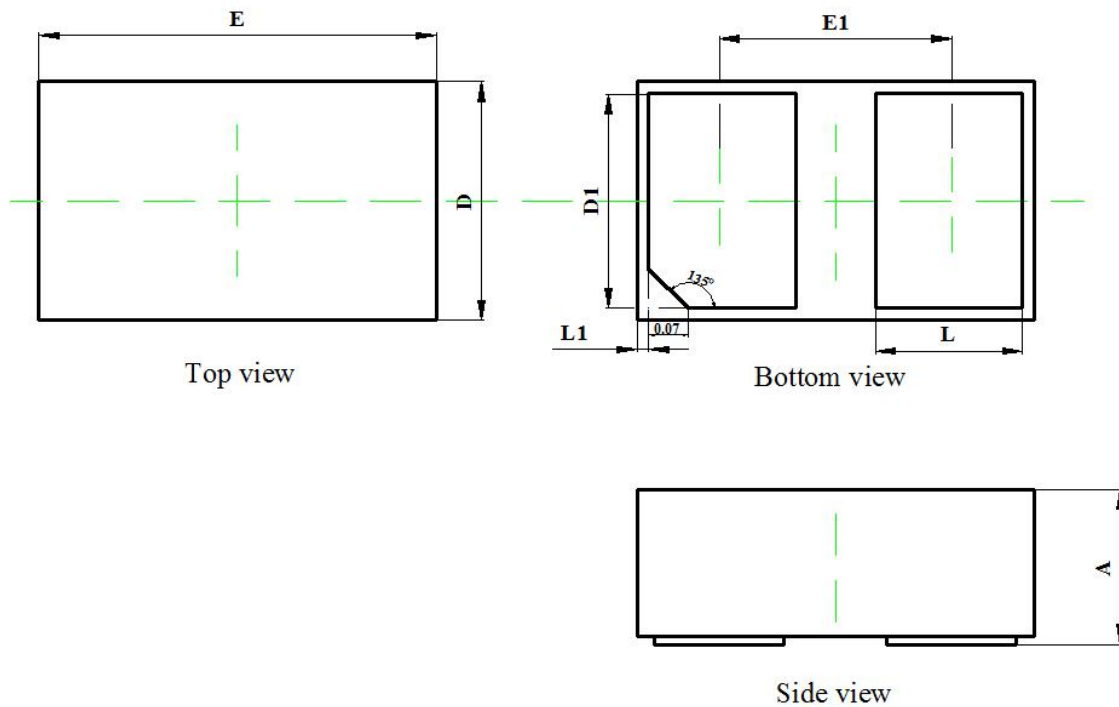


Fig.4 IV Curve (Forward Voltage)



9. Package Outline Dimensions

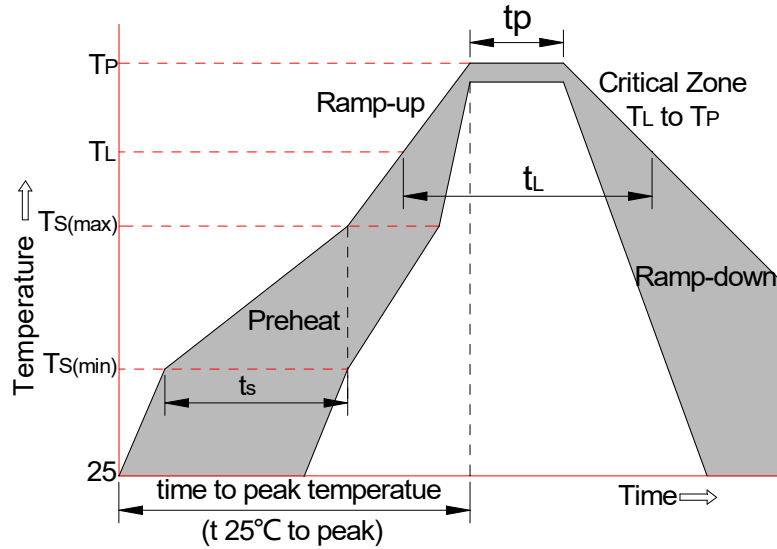
DFN1006 Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.350	0.450	0.014	0.018
D	0.550	0.650	0.022	0.026
E	0.950	1.050	0.037	0.041
D1	0.420	0.520	0.017	0.020
E1	0.550	0.650	0.022	0.026
L	0.270	0.370	0.011	0.015
L1	0.000	0.100	0.000	0.004



10. Soldering Parameters



Reflow Condition		Pb-Free Assembly
Pre-heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
xTime 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



11. Contact Information

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Please e-mail us at: sales1@wdsemi.com

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